

LN52

GaAs Infrared Light Emitting Diode

For optical control systems

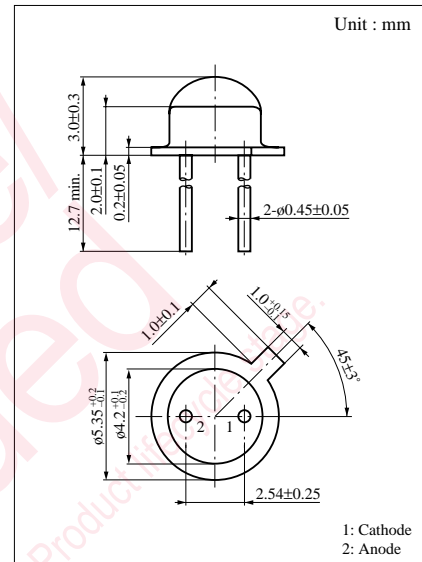
■ Features

- High-power output, high-efficiency : $P_O = 6 \text{ mW (typ.)}$
- Wide directivity, matched for external optical systems : $\theta = 100 \text{ deg.}$
- Infrared light emission close to monochromatic light : $\lambda_p = 950 \text{ nm}$
- Optimum for measuring instruments and control equipments in combination with silicon photodetectors

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

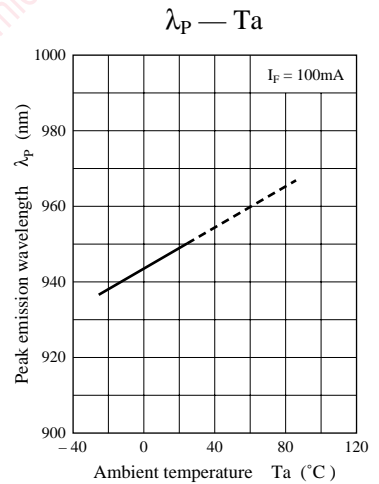
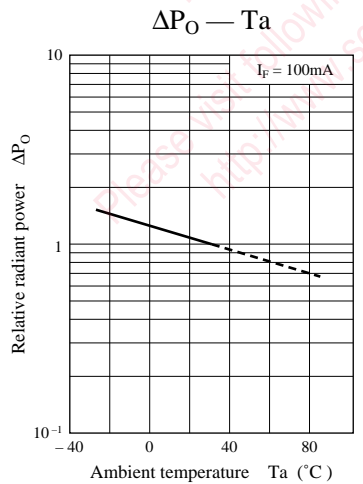
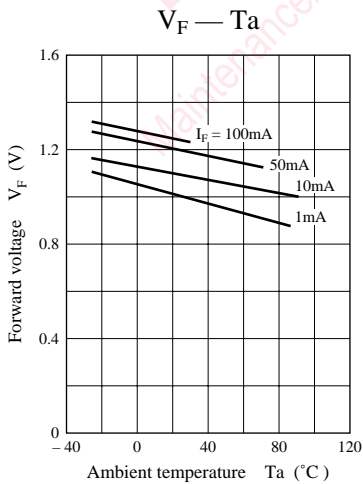
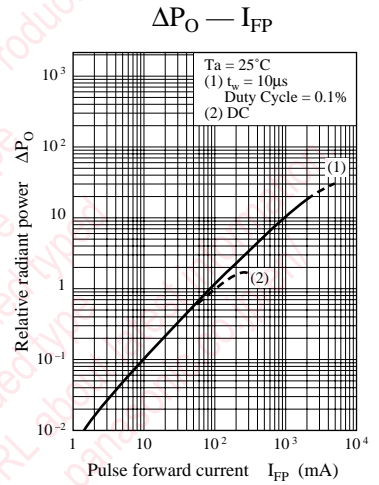
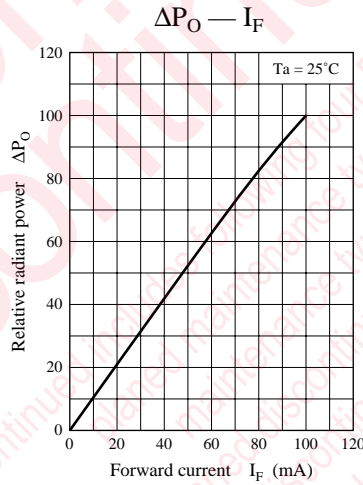
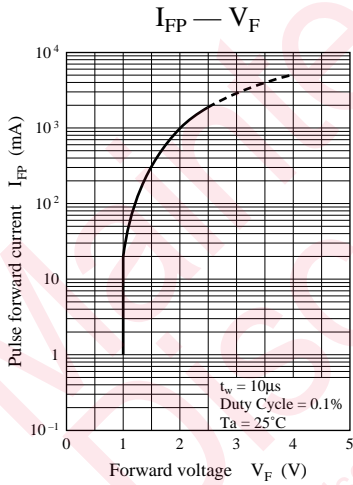
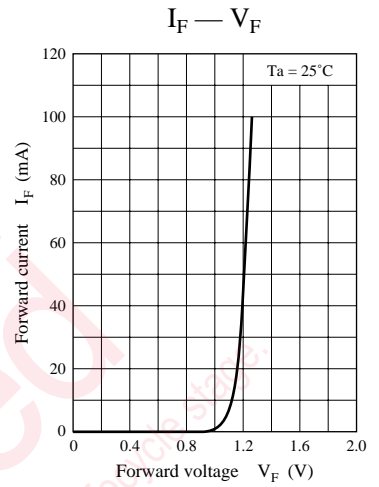
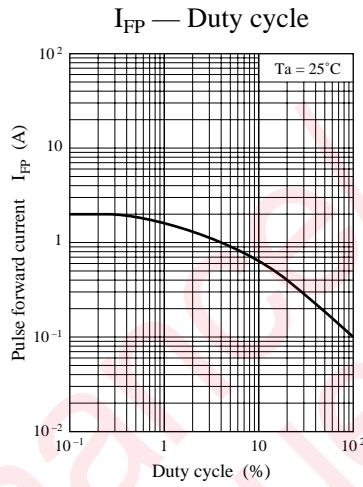
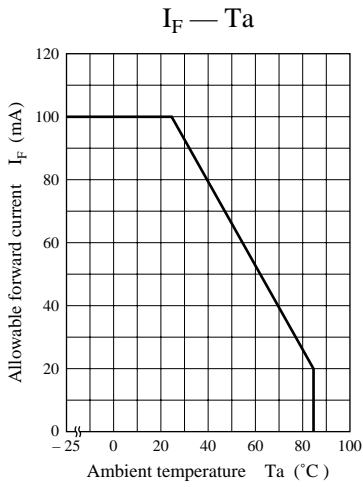
Parameter	Symbol	Ratings	Unit
Power dissipation	P_D	160	mW
Forward current (DC)	I_F	100	mA
Pulse forward current	I_{FP}^*	2	A
Reverse voltage (DC)	V_R	3	V
Operating ambient temperature	T_{opr}	-25 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}	-30 to +100	$^\circ\text{C}$

* $f = 100 \text{ Hz}$, Duty cycle = 0.1 %

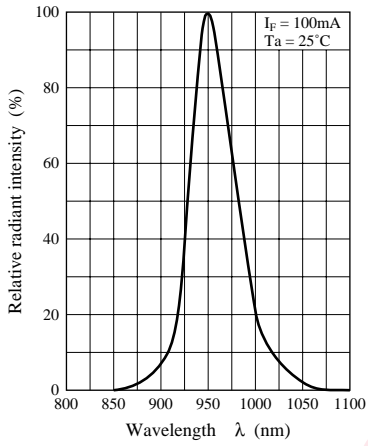


■ Electro-Optical Characteristics ($T_a = 25^\circ\text{C}$)

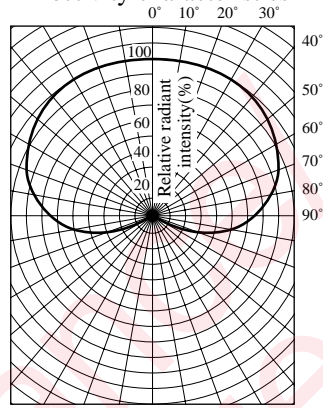
Parameter	Symbol	Conditions	min	typ	max	Unit
Radiant power	P_O	$I_F = 100\text{mA}$	3.5	6		mW
Peak emission wavelength	λ_p	$I_F = 100\text{mA}$		950		nm
Spectral half band width	$\Delta\lambda$	$I_F = 100\text{mA}$		50		nm
Forward voltage (DC)	V_F	$I_F = 100\text{mA}$		1.25	1.6	V
Reverse current (DC)	I_R	$V_R = 3\text{V}$			10	μA
Capacitance between pins	C_t	$V_R = 0\text{V}$, $f = 1\text{MHz}$		50		pF
Rise time	t_r	$I_{FP} = 100\text{mA}$		1		μs
Fall time	t_f			1		μs
Half-power angle	θ	The angle in which radiant intensity is 50%		100		deg.



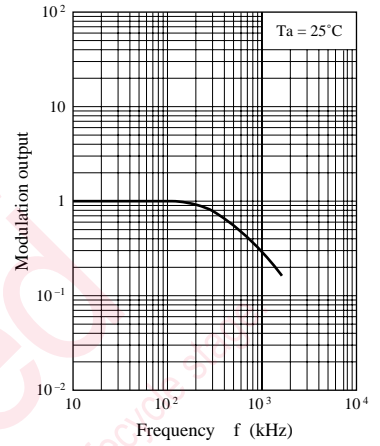
Spectral characteristics



Directivity characteristics



Frequency characteristics



Maintenance/Discontinued includes following four Product life cycle types:
 planned maintenance type
 maintenance type
 planned discontinued type
 discontinued type
 Please visit following URL about latest information.
<http://www.semicon.panasonic.co.jp/en/>

Caution for Safety

 **DANGER**

■ This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.

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